

Plasma-Surface Interactions (PSI): Atomistic Insights into He Transport and Agglomeration in Plasma-Exposed Tungsten

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Project web site: <https://collab.mcs.anl.gov/display/PSIscidac/>



Introduction

- Experimentally observed tungsten (W) surface dynamics under combined thermal/particle fluxes**
 - $T < 700$ K: non-specific damage
 - 900 K $< T < 1900$ K: fuzz / coral
 - $T > 2000$ K: holes
- Small-scale MD simulations reveal continual bubble formation, bursting, and W surface modification**
 - Observed near-surface structure: He cluster/bubble distribution (blue spheres), W adatoms (purple spheres), and sub-surface W atoms (grey spheres).
 - Configuration shown after $\sim 2 \times 10^{20}$ He/m², but with a very high implantation rate of 10^{27} He/(m²s), i.e., about 5 orders of magnitude too large!
- Solid Surface Modeling Roadmap**
 - Low-temperature ($< \sim 1000$ K) regime of low energy (~ 100 eV).
 - He (later mixed He-H) plasma exposure to tungsten: focus on bubble formation, growth, and over-pressurization leading to tungsten surface morphology changes.
- Key Physics Questions:**
 - Rate effects (explored by AMD, MD and KMC simulations) versus continuum reaction-diffusion model predictions and experimental measurements
 - Validity of dilute-limit approximation in concentrated He bubble populations
 - Introduction of drift (driven diffusion) into transport formalism due to interaction of clusters with sinks such as surface and grain boundaries
 - Multiscale integration

Bulk diffusion of Small He Clusters

- To parameterize macroscopic reaction-diffusion models, we rely on atomistic simulations to identify unit transport/reaction mechanisms.
- Using a combination of MD and Accelerated MD (AMD), we have investigated the bulk diffusion of small He clusters, with sizes ranging between 1 and 8.
 - With AMD: Find and analyze the dominant diffusion pathways at low temperatures
 - With MD: Compute the diffusivity of the clusters between 250 and 1400 K. Assess whether the low-T kinetics hold at operation temperatures
- Diffusion Pathways and Energetics**
 - Pathways become increasingly complex with cluster size. They typically contain many intermediate states, suggesting that entropic effects may play an important role in the diffusion dynamics.
- Kinetics**
 - At higher temperatures, relevant for reactor conditions, the entropic effects of the multiple minima exert themselves.
 - For all cluster sizes, the cluster mobility can be accounted for by the pathway identified with AMD, over the entire temperature range.
 - The non-Arrhenius temperature dependence can be captured by a generalized transition-state theory that accounts for intermediate states (green curve on the right).
 - Larger clusters (≥ 7) quickly experience *trap mutation*, i.e., the formation of a bubble nucleus by the creation of a W vacancy-interstitial (Frenkel) pair. Once bound to a vacancy, He clusters are essentially immobile.
 - Our combined MD/AMD approach provides a comprehensive picture of the unit mechanisms of the diffusion of small He clusters in bulk W:
 - Relevant diffusion pathways have been identified
 - Diffusivity has been characterized over a wide range of temperatures

Dynamics of Mobile He Clusters near W Surfaces: Drift due to Surface Segregation and Near-surface Kinetic Processes

- Motivation for this study:** The diffusional transport of mobile He clusters mediates the evolution of surface morphology and the structural evolution of the near-surface regions of the plasma-exposed material.
- Molecular-statics computations:** Energy profiles of different-size He clusters near W surfaces indicate that the surface is a sink for He clusters. Case: W(100)
- Tri-He cluster kinetic processes near W(100) surface:**
 - Tri-He (a) and Tri-He (b) energy profiles showing drift, trap mutation, and dissociation/desorption.
- Di-He cluster kinetic processes near W(100) surface:**
 - Di-He (a) and Di-He (b) energy profiles showing drift, trap mutation, and dissociation/desorption.
- He Agglomeration in Near-Surface Regions of Polycrystalline Tungsten: Surface and Grain-Boundary (GB) Segregation**
 - Large-scale MD simulations of He aggregation in a model of polycrystalline tungsten reveal transport of He atoms (drift-diffusion), their aggregation to form He bubbles, and the growth of He bubbles.
 - Schematic representation of supercell with two GBs for large-scale MD simulations.
 - He depth distribution from MD simulations of He implantation.
 - Energy profile of tri-He cluster near GB.
 - Distribution of He atoms from large-scale MD simulations of He aggregation in polycrystalline tungsten.
- Setup of the large-scale MD simulations:**
 - GB type: $\Sigma 3 <101>$ {121} symmetric tilt GB with a W(111) free surface
 - Simulation cell size: 50 nm \times 50 nm \times 18 nm
 - Number of W atoms in simulation cell: 2.4 million
 - Distance between GBs: 25 nm
 - Rate of He atom insertion: 1 every 10 ps
 - Implantation depth distributions for the insertion of He atoms into the W matrix derived based on MD simulations of He-atom impingement onto W surfaces
- MD results show that GBs and W surface serve as sinks for He atoms
- Calculations of He small-cluster energetics as a function of cluster distance from grain boundaries in W and from the W surface aid in providing thermodynamic and kinetic interpretations of the He bubble formation processes observed in the MD simulations

Helium Bubble Growth

- In addition to the migration behavior of small He clusters, the behavior of large He bubbles is critical for parameterizing reaction-diffusion models and understanding the morphological evolution of the surface.
 - As shown in the MD simulation on the left, once clusters undergo trap mutation, they act as bubble nuclei. Subsequently, these bubbles grow by absorbing mobile He clusters.
 - To understand the effect of the He absorption rate on the bubble evolution, we perform AMD simulations of the growth of single bubbles at carefully controlled rates.
- We use parallel replica dynamics (ParRep). ParRep allows for the temporal parallelization of the discrete state-to-state dynamics and, therefore, greatly increases the time scale amenable to direct simulation.
 - For example, by using 12000 cores, we were able to reach simulation times of 7.25 μ s, which allows the simulation of realistic growth rates.
- Our results indicate that the average bubble size right before bursting is very sensitive to the growth rate: decreasing the growth rate leads to bursting at smaller sizes.
 - To explain this behavior, we tracked (a) the motion of the bubble's center of mass and (b) the maximum depth reached by He atoms as a function of the number of He atoms.
 - Slow growing bubbles grow preferentially towards the surface, while faster growing bubbles grow more isotropically (c).
 - In the latter case, bursting is delayed, as more He atoms are required for the bubbles to reach the surface and burst.

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